

**Method for producing semiconductor wafers composed of
silicon**

Abstract

A method for producing semiconductor wafers composed of silicon, comprising
pulling a single crystal at a seed crystal from a melt heated in a crucible;
supplying heat to the center of the crucible bottom with a heating power which, in the course of a cylindrical section of the single crystal being pulled, is increased at least once to not less than 2 kW and is then decreased again; and
slicing the semiconductor wafers from the pulled single crystal.

Figure 1